



PTO/SB/08a/b (08-03)

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Substitute for form 1449A/B/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)				<b>Complete if Known</b>	
				Application Number	10/769,787-Conf. #9244
				Filing Date	February 3, 2004
				First Named Inventor	John T. Moore
				Art Unit	2812-2822
				Examiner Name	Not Yet Assigned T.M. Thomas
Sheet	1	of	3	Attorney Docket Number	M4065.0989/P989-A

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
JMS	A	US 2004/0035401	2/2004	Ramachandran et al.	
	B	US 2003/0212724	11/2003	Ovshinsky et al.	
	C	US 2003/0048744	3/2003	Ovshinsky et al.	
	D	US 2003/0212725	11/2003	Ovshinsky et al.	
	E	US RE 37,259E	7/2001	Ovshinsky	
	F	US 3,271,591	9/1966	Ovshinsky	
	G	US 3,961,314	6/1976	Klose et al.	
	H	US 3,966,317	6/1976	Wacks et al.	
	I	US 3,983,542	11/1976	Ovshinsky	
	J	US 3,988,720	10/1976	Ovshinsky	
	K	US 4,177,474	12/1979	Ovshinsky	
	L	US 4,267,261	5/1981	Hallman et al.	
	M	US 4,597,162	7/1986	Johnson et al.	
	N	US 4,608,296	8/1986	Keem et al.	
	O	US 4,637,895	1/1987	Ovshinsky et al.	
	P	US 4,646,266	2/1987	Ovshinsky et al.	
	Q	US 4,664,939	5/1987	Ovshinsky	
	R	US 4,668,968	5/1987	Ovshinsky et al.	
	S	US 4,670,763	6/1987	Ovshinsky et al.	
	T	US 4,673,957	6/1987	Ovshinsky et al.	
	U	US 4,678,679	7/1987	Ovshinsky	
	V	US 4,696,758	9/1987	Ovshinsky et al.	
	W	US 4,698,234	10/1987	Ovshinsky et al.	
	X	US 4,710,899	12/1987	Young et al.	
	Y	US 4,728,406	3/1988	Banerjee et al.	
	Z	US 4,737,379	4/1988	Hudgens et al.	
	A1	US 4,766,471	8/1988	Ovshinsky et al.	
	B1	US 4,769,338	9/1988	Ovshinsky et al.	
	C1	US 4,775,425	10/1988	Guha et al.	
	D1	US 4,788,594	11/1988	Ovshinsky et al.	
	E1	US 4,809,044	2/1989	Pryor et al.	
	F1	US 4,818,717	4/1989	Johnson et al.	
	G1	US 4,843,443	6/1989	Ovshinsky et al.	
	H1	US 4,845,533	7/1989	Pryor et al.	
	I1	US 4,853,785	8/1989	Ovshinsky et al.	
	J1	US 4,891,330	1/1990	Guha et al.	
	K1	US 5,128,099	7/1992	Strand et al.	
	L1	US 5,159,661	10/1992	Ovshinsky et al.	
	M1	US 5,166,758	11/1992	Ovshinsky et al.	
	N1	US 5,177,567	1/1993	Klersy et al.	
JMS	O1	US 5,296,716	3/1994	Ovshinsky et al.	

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JmJ	P1	US 5,335,219	8/1994	Ovshinsky et al.	
	Q1	US 5,359,205	10/1994	Ovshinsky	
	R1	US 5,341,328	8/1994	Ovshinsky et al.	
	S1	US 5,406,509	4/1995	Ovshinsky et al.	
	T1	US 5,414,271	5/1995	Ovshinsky et al.	
	U1	US 5,534,711	7/1996	Ovshinsky et al.	
	V1	US 5,534,712	7/1996	Ovshinsky et al.	
	W1	US 5,536,947	7/1996	Klersy et al.	
	X1	US 5,543,737	8/1996	Ovshinsky	
	Y1	US 5,591,501	1/1997	Ovshinsky et al.	
	Z1	US 5,596,522	1/1997	Ovshinsky et al.	
	A2	US 5,687,112	11/1997	Ovshinsky	
	B2	US 5,694,054	12/1997	Ovshinsky et al.	
	C2	US 5,714,768	2/1998	Ovshinsky et al.	
	D2	US 5,825,046	10/1998	Czubatyj et al.	
	E2	US 5,912,839	6/1999	Ovshinsky et al.	
	F2	US 5,933,365	8/1999	Klersy et al.	
	G2	US 6,011,757	1/2000	Ovshinsky	
	H2	US 6,087,674	7/2000	Ovshinsky et al.	
	I2	US 6,141,241	10/2000	Ovshinsky et al.	
	J2	US 6,339,544	1/2002	Chiang et al.	
	K2	US 6,404,665	6/2002	Lowery et al.	
	L2	US 6,429,064	8/2002	Wicker	
	M2	US 6,437,383	8/2002	Xu	
	N2	US 6,462,984	10/2002	Xu et al.	
	O2	US 6,480,438	11/2002	Park	
	P2	US 6,487,113	11/2002	Park et al.	
	Q2	US 6,501,111	12/2002	Lowery	
	R2	US 6,507,061	1/2003	Hudgens et al.	
	S2	US 6,511,862	1/2003	Hudgens et al.	
	T2	US 6,511,867	1/2003	Lowery et al.	
	U2	US 6,512,241	1/2003	Lai	
	V2	US 6,514,805	2/2003	Xu et al.	
	W2	US 6,531,373	3/2003	Gill et al.	
	X2	US 6,534,781	3/2003	Dennison	
	Y2	US 6,545,287	4/2003	Chiang	
	Z2	US 6,545,907	4/2003	Lowery et al.	
	A3	US 6,555,860	4/2003	Lowery et al.	
	B3	US 6,563,164	5/2003	Lowery et al.	
	C3	US 6,566,700	5/2003	Xu	
	D3	US 6,567,293	5/2003	Lowery et al.	
	E3	US 6,569,705	5/2003	Chiang et al.	
	F3	US 6,570,784	5/2003	Lowery	
	G3	US 6,576,921	6/2003	Lowery	
JmJ	H3	US 6,586,761	7/2003	Lowery	

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10/769,787	I3	US 6,589,714	7/2003	Maimon et al.	
	J3	US 6,590,807	7/2003	Lowery	
	K3	US 6,593,176	7/2003	Dennison	
	L3	US 6,597,009	7/2003	Wicker	
	M3	US 6,605,527	8/2003	Dennison et al.	
	N3	US 6,613,604	9/2003	Maimon et al.	
	O3	US 6,621,095	9/2003	Chiang et al.	
	P3	US 6,625,054	9/2003	Lowery et al.	
	Q3	US 6,642,102	11/2003	Xu	
	R3	US 6,646,297	11/2003	Dennison	
	S3	US 6,649,928	11/2003	Dennison	
	T3	US 6,667,900	12/2003	Lowery et al.	
	U3	US 6,671,710	12/2003	Ovshinsky et al.	
	V3	US 6,673,648	1/2004	Lowrey	
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	X3	US 6,674,115	1/2004	Hudgens et al.	
	Y3	US 6,687,427	2/2004	Ramalingam et al.	
	Z3	US 6,690,026	2/2004	Peterson	
	A4	US 6,696,355	2/2004	Dennison	
	B4	US 6,687,153	2/2004	Lowery	
	C4	US 6,707,712	3/2004	Lowery	
10/769,787	D4	US 6,714,954	3/2004	Ovshinsky et al.	

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Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup>	Number <sup>4</sup> and Code <sup>5</sup> (if known)				

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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.

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				Filing Date	Concurrently Herewith
				First Named Inventor	John T. Moore, et al.
				Art Unit	<del>N/A</del> 2822
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U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.†	Document Number Number-Kind Code² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
JMT	AB**	2002/0072188	6/13/2002	Gilton	
	AC**	2002/0106849	08/08/2002	Moore	
	AH**	2002/0123169	09/05/2002	Moore et al.	
	AI**	2002/0123170	09/05/2002	Moore et al.	
	AJ**	2002/0123248	09/05/2002	Moore et al.	
	AK**	2002/0127886	09/12/2002	Moore et al.	
	AL**	2002/0132417	09/09/2002	Li	
	**	2002/0160551	10/31/2002	Harshfield	
	AF**	2002/0163828	11/07/2002	Krieger et al.	
	AM**	2002/0168852	11/14/2002	Harshfield et al.	
	AN**	2002/0190289	12/19/2002	Harshfield et al.	
	AP**	2003/0001229	01/02/2003	Moore et al.	
	AQ**	2003/0027416	02/06/2003	Moore	
	AR**	2003/0032254	02/13/2003	Gilton	
	AU**	2003/0038301	02/27/2003	Moore	
	AV**	2003/0043631	03/06/2003	Gilton et al.	
	AW**	2003/0045049	03/06/2003	Campbell et al.	
	AX**	2003/0045054	03/06/2003	Campbell et al.	
	AY**	2003/0047765	03/13/2003	Campbell	
	AZ**	2003/0047772	03/13/2003	Li	
	AA1**	2003/0047773	03/13/2003	Li	
	AC1**	2003/0049912	03/13/2003	Campbell et al.	
	AD1**	2003/0068861	04/10/2003	Li	
	AE1**	2003/0068862	04/10/2003	Li	
	AF1**	2003/0095426	05/22/2003	Hush et al.	
	AG1**	2003/0096497	05/22/2003	Moore et al.	
	AH1**	2003/0107105	06/12/2003	Kozicki	
	AI1**	2003/0117831	06/26/2003	Hush	
	AJ1**	2003/0128612	07/10/2003	Moore et al.	
	AK1**	2003/0137869	07/24/2003	Kozicki	
	AL1**	2003/0143782	07/31/2003	Gilton et al.	
	**	2003/1055589	08/21/2003	Campbell et al.	
	**	2003/0155606	08/21/2003	Campbell et al.	
	AM1**	2003/0156447	08/21/2003	Kozicki	
	AN1**	2003/0156463	08/21/2003	Casper et al.	
	AO1**	3,622,319	11/1971	Sharp	
	AP1**	3,743,847	7/1973	Boland	
	AQ1**	4,269,935	5/1981	Masters et al.	
	AR1**	4,312,938	1/1982	Drexler, et al.	
	AS1**	4,316,946	1/1982	Masters, et al.	
	AT1**	4,320,191	3/1982	Yoshikawa et al.	
	AU1**	4,405,710	9/1983	Balasubramanyam et al.	
	AV1**	4,419,421	12/1983	Wichelhaus, et al.	
JMT	AW1**	4,499,557	2/1985	Holmberg et al.	

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				First Named Inventor	John T. Moore, et al.
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Sheet	2	of	11	Attorney Docket Number	M4065.0989/P989-A

JMJ	AX1**	4,671,618	06/09/1987	Wu et al.	
	AY1**	4,795,657	1/1989	Formigoni et al.	
	AZ1**	4,800,526	01/24/1989	Lewis	
	AA2**	4,847,674	7/1989	Sliwa et al.	
	AB2**	5,177,567	1/1993	Klersy et al.	
	AC2**	5,219,788	6/1993	Abermathey et al.	
	AD2**	5,238,862	8/1993	Blalock et al.	
	AE2**	5,272,359	12/21/1993	Nagasubramanian et al.	
	AF2**	5,314,772	5/24/1994	Kozicki	
	AG2**	5,315,131	5/1994	Kishimoto et al.	
	AH2**	5,350,484	9/1994	Gardner et al.	
	AI2**	5,360,981	11/1994	Owen et al.	
	AJ2**	5,500,532	3/19/1996	Kozicki et al.	
	AK2**	5,512,328	4/1996	Yoshimura et al.	
	AL2**	5,512,773	4/1996	Wolf et al.	
	AM2**	5,726,083	3/1998	Takaishi	
	AN2**	5,751,012	5/12/1998	Wolstenholme et al.	
	AP2**	5,789,277	8/1998	Zahorik et al.	
	**	5,814,527	9/29/1998	Wolstenholme et al.	
	**	5,818,749	10/06/1998	Harshfield	
	AQ2**	5,841,150	11/1998	Gonzalez et al.	
	AR2**	5,846,889	12/1998	Harbison et al.	
	**	5,851,882	12/22/1998	Harshfield	
	**	5,869,843	2/9/1999	Harshfield	
	AU2**	5,920,788	7/1999	Reinberg	
	AV2**	5,998,066	12/1999	Block et al.	
	**	6,031,287	2/29/2000	Harshfield	
	AW2**	6,072,716	06/06/2000	Jacobson et al.	
	AX2**	6,077,729	6/2000	Harshfield	
	AZ2**	6,177,338	1/2001	Liaw et al.	
	AA3**	6,117,720	9/2000	Harshfield	
	AB3**	6,143,604	11/2000	Chiang et al.	
	AC3**	6,236,059	5/2001	Wolsteinholme et al.	
	AD3**	6,297,170	10/2001	Gabriel et al.	
	AE3**	6,300,684	10/2001	Gonzalez et al.	
	AF3**	6,316,784	11/2001	Zahorik et al.	
	AG3**	6,329,606	12/2001	Freyman et al.	
	AH3**	6,348,365	2/19/2002	Moore et al.	
	AI3**	6,350,679	2/2002	McDaniel et al.	
	AJ3**	6,376,284	4/2002	Gonzalez et al.	
	AL3**	6,391,688	5/2002	Gonzalez et al.	
	AM3**	6,414,376	7/2002	Thakur et al.	
	**	6,420,725	7/16/2002	Harshfield	
	AQ3**	6,423,628	7/2002	Li et al.	
	**	6,440,837	8/27/2002	Harshfield	
	AQ3**	6,473,332	10/2002	Ignatiev et al.	
	**	5,761,115	06/02/98	Kozicki, et al.	
	**	5,896,312	04/20/99	Kozicki, et al.	
JMJ	**	5,914,893	06/22/99	Kozicki, et al.	

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Examiner Name	<del>Not Yet Assigned</del> T.M. Thomas				
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JMT	**	6,084,796	07/04/00	Kozicki, et al.	
	**	2002/0000666	01/03/02	Kozicki	
	**	6,388,324	05/14/02	Kozicki	
	**	6,418,049	07/09/02	Kozicki, et al.	
	**	6,469,364	10/22/02	Kozicki	
	**	6,487,106	11/26/02	Kozicki	
	**	2002/0168820	11/14/02	Kozicki, et al.	
	**	2002/0190350	12/19/02	Kozicki, et al.	
	**	2003/0035314	02/20/03	Kozicki	
	**	2003/0035315	02/20/03	Kozicki	
JMT	**	2003/0048519	03/13/03	Kozicki	

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		Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)					
JMT	BA**	56126916		10/19981	Akira et al.		
	BB**	97/48032		12/18/97	WO		
	BC**	99/28914		06/10/99	WO		
	BD**	00/48196		08/17/00	WO		
	BE**	02/21542 A1		03/14/02	WO		
JMT	BF**	02/082452 A2		10/17/02	WO		

Examiner Signature	T. M. Thomas	Date Considered	00-20-05
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		Application Number	10/231,779
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		Filing Date	August 29, 2002
		First Named Inventor	Moore, John T.
		Group Art Unit	<del>2818</del> 2822
		Examiner Name	Nhu, D. T. M. Thomas
		Attorney Docket Number	M4065.0989/P989
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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
JMJ	CA**	Abdel-All, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge <sub>5</sub> As <sub>38</sub> Te <sub>57</sub> chalcogenide glass, Vacuum 59 (2000) 845-853.	
	CB**	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189.	
	CC**	Adler, D.; Henisch, H.K.; Mott, S.N., The mechanism of threshold switching in amorphous alloys, Rev. Mod. Phys. 50 (1978) 209-220.	
	CD**	Afifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se <sub>75</sub> Ge <sub>25</sub> -xSbx, Appl. Phys. A 55 (1992) 167-169.	
	CE**	Afifi, M.A.; Labib, H.H.; Fouad, S.S.; El-Shazly, A.A., Electrical & thermal conductivity of the amorphous semiconductor GexSe <sub>1-x</sub> , Egypt, J. Phys. 17 (1986) 335-342.	
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Substitute for form 1449B/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)				<b>Complete if Known</b>	
				Application Number	10/231,779
				Filing Date	August 29, 2002
				First Named Inventor	Moore, John T.
				Group Art Unit	2848 JB22
				Examiner Name	Nhu, D. T. M. Thomas
Sheet	10	of	11	Attorney Docket Number	M4065.0989/P989

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		Group Art Unit	<del>2818</del> 2822
		Examiner Name	Nhu, D. T. M. Thomas
Sheet	11	of	11
		Attorney Docket Number	M4065.0989/P989

JMJ	CJ6**	Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A. M.; Dexpert, H.; Lagarde, J. P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and exafs structural investigation, Transport-structure relations in fast ion and mixed conductors Proceedings of the 6th Riso International symposium. 9-13 September 1985.
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Examiner Signature	T. M. Thomas	Date Considered	06-22-05
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